

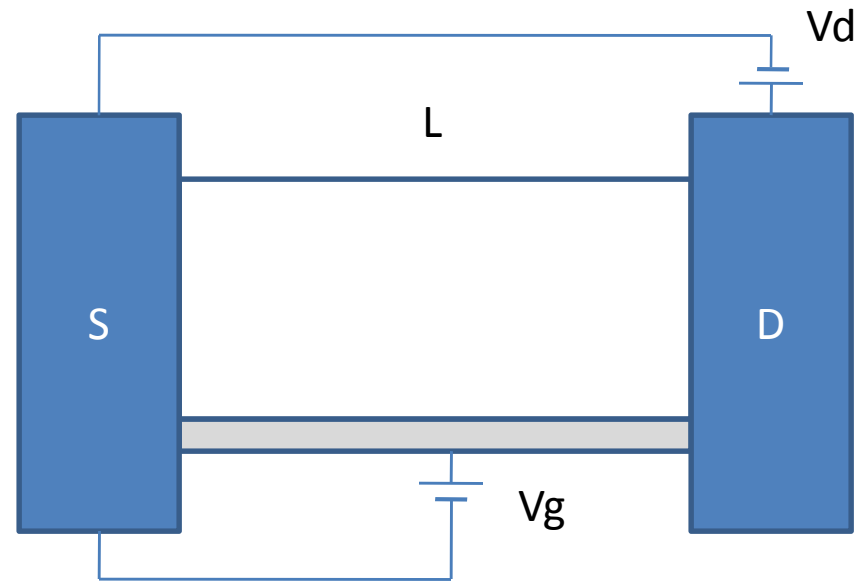
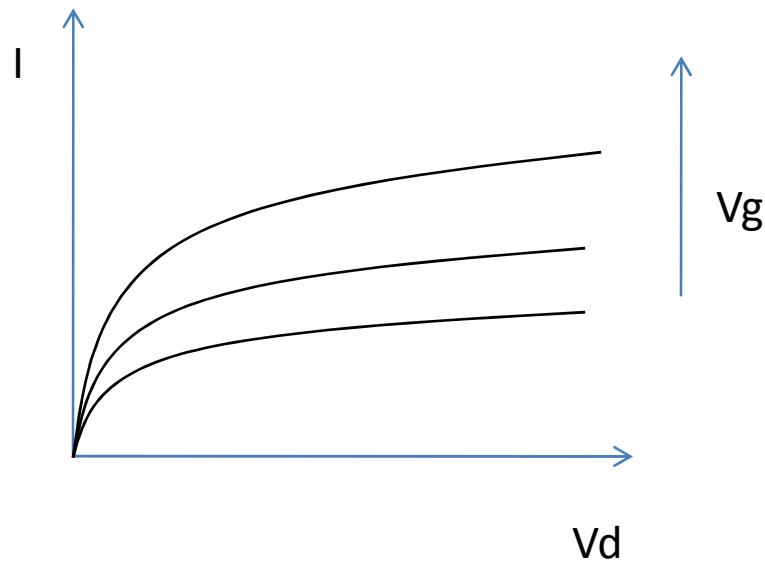
ECE 659 Quantum Transport: Atom to Transistor

Lecture 1: Introduction

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- Field Effect Transistor is the most common device today
- Modern day processors have a billion each
- It is a resistor whose resistance can be controlled
- The third terminal, gate (V_g), controls the resistance
- V_d drives the current through the device



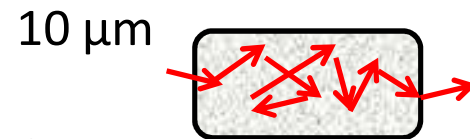
Typically V_d varies from 0.5V to 1V,
 R varies from 10k to 100M*

Other interesting device:

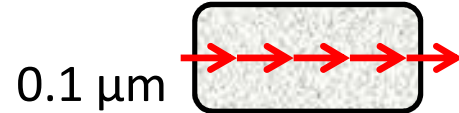
- Energy Conversion devices
- Sensors

*The online lecture shows the variation as 10k to 1M,
 these notes present the correct value

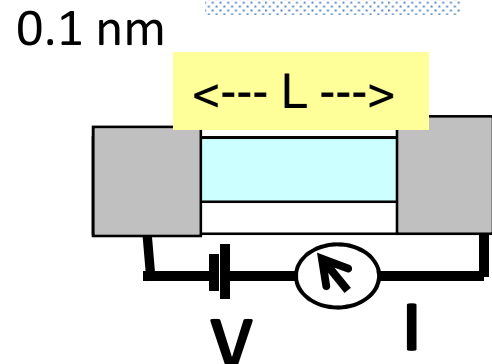
0.1 mm Macroscopic dimensions



1 μm



1 nm Atomic dimensions



Ohm's Law \Rightarrow

$$R = \frac{\rho L}{A}$$

$$G = \frac{\sigma A}{L}$$

Does it make sense to talk about resistance of very small conductor?
Yes. It does.

\longrightarrow Present commercial technology

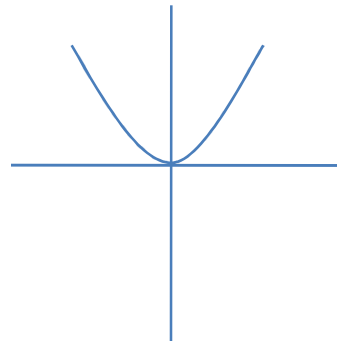
Top down approach:

$$\sigma = qn \frac{q\tau}{m}$$

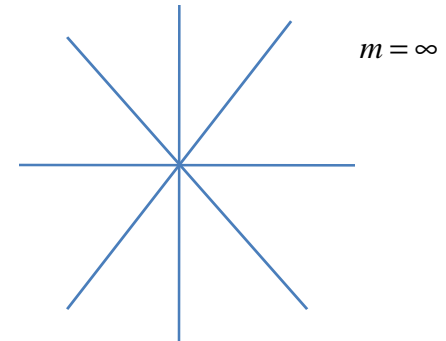
Electron density

Mean free time

Effective mass



$$\frac{1}{m} = \frac{1}{\hbar^2} \frac{d^2 E}{dk^2}$$

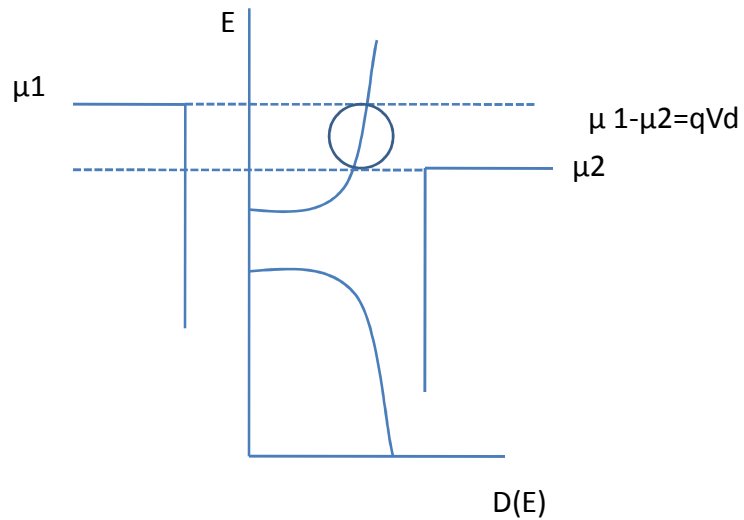


Quantum of Conductance

$$G = \frac{q^2}{h} (\pi D \gamma)$$

\searrow
 $\frac{1}{25k\Omega}$

D -> density of states



$$\frac{\gamma}{h} = \text{Rate at which electrons can come out and go into channel}$$

$$D \sim AL$$

$$\gamma \sim \frac{1}{L} \longrightarrow \text{Ballistic transport}$$

$$\gamma \sim \frac{1}{L^2} \longrightarrow \text{Diffusive transport}$$